Heavy Ion Microbeam- and Broadbeam-Induced Current Transients in SiGe HBTs

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• Department of Physics at the University of Jyväskylä, Finland (JYFL)
• Grand Accélérateur National d’Ions Lourds, France (GANIL)
Heavy ion transient overview

- **IBM 5AM SiGe HBT** is device-under-test
- High-speed measurement setup
- Low-impedance current transient measurements
  - SNL, JYFL, GANIL
- Microbeam to broadbeam position inference
- Improvement to state-of-the-art

2.9 mm connectors

1.5 in

Single SiGe HBT device under test (1 mm²)

Bias conditions of interest

All biases based on device isolation

3-D TCAD from DUT GDSII
IBM 5AM npn SiGe HBT

Bias conditions chosen to represent “circuit-like” experiments
Typical experimental setup

Different than broadbeam

36 MeV $^{16}$O dE/dx profile [SRIM-2008]

Sandia National Laboratories’ Microbeam Chamber
Device under test and microbeam irradiation

Active junction area
Microbeam rastering concept

IBM 5AM npn SiGe HBT

Microbeam data allows position correlation

36 MeV $^{16}$O SNL microbeam: Case 1

Peak current magnitude

Base

Collector

- $V_{\text{sub}} = -4$ V; all other terminals grounded
- Base terminal images base-collector junction
- Collector terminal images base-collector junction and subcollector

Active base-collector junction area

Imaging provides information about position and current
36 MeV $^{16}$O SNL microbeam: Case 2 vs. 3

Peak current magnitude

$V_C = +3$ V (Case 2)

$V_{sub} = -3$ V (Case 3)

• Same result was observed in two-photon pulsed laser testing


Difference in peak current results from non-zero $V_{CB}$
Heavy ion broadbeam transients

- Data collection at JYFL and GANIL
- 9.3 MeV/u cocktail including $^{20}\text{Ne}$, $^{40}\text{Ar}$, $^{82}\text{Kr}$, and $^{131}\text{Xe}$ and 45.5 MeV/u $^{136}\text{Xe}$

IBM 5AM npn SiGe HBT

University of Jyväskylä
K-130 Cyclotron

No position correlation with broadbeam irradiation
JYFL vs. SNL: LET scaling

A $^{20}$Ne and $^{16}$O transients are similar – related by LET
JYFL: LET extremes

Position correlation made possible with microbeam data

- $^20\text{Ne}$ LET: $3.6\text{ (MeV·cm}^2\text{/mg)}$
- $^{131}\text{Xe}$ LET: $60\text{ (MeV·cm}^2\text{/mg)}$

- $9.3\text{ MeV/u}$
JYFL vs. GANIL transients

Similar LET values produce different transient responses.

Maximum observed transients for each ion at each facility:

- JYFL
- GANIL

Track structure
Recombination

$^{82}\text{Kr}$ vs. $^{136}\text{Xe}$

32 (MeV·cm$^2$/mg)
27 (MeV·cm$^2$/mg)

$^{82}\text{Kr}$ @ 9.3 MeV/u
$^{136}\text{Xe}$ @ 45.5 MeV/u
Conclusions

• Microbeam (SNL) transients reveal position-dependent heavy ion response
  • Unique response for different device regions
  • Unique response for different bias schemes
  • Similarities to TPA pulsed-laser data

• Broadbeam transients (JYFL and GANIL) provide realistic heavy ion response
  • Feedback using microbeam data
  • Overcome issues of LET and ion range with microbeam
  • **Angled $^{40}$Ar data in full paper

• Data sets yield first-order results, suitable for TCAD calibration feedback